

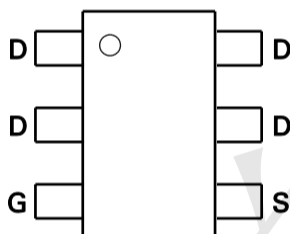
Product Summary

- 60V/-3A
 $R_{DS(ON)} = 95m\Omega$ (Typ) @ $V_{GS} = -10V$
 $R_{DS(ON)} = 130m\Omega$ (Typ) @ $V_{GS} = -4.5V$
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

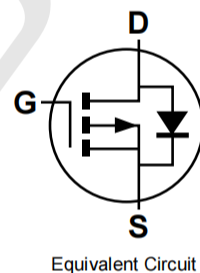
Application

- DC-DC Converters.
- Load Switch.
- Power Management.

Package and Pin Configuration



Circuit diagram



Marking: **P 603P**

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-60	V
Gate-Source Voltage			V_{GS}	± 20	V
Continuous Drain Current	$V_{GS} = -10V$	(Note 6)	I_D	-3	A
		$T_A = +70^\circ C$ (Note 6)		-2.4	
		(Note 5)		-2.3	
Pulsed Drain Current	$V_{GS} = -10V$	(Note 7)	I_{DM}	-13.6	A
Continuous Source Current (Body Diode)			I_S	-2.5	A
Pulsed Source Current (Body Diode)			I_{SM}	-13.6	A

Thermal Characteristics (@ $T_A = +25^\circ C$, unless otherwise specified.)

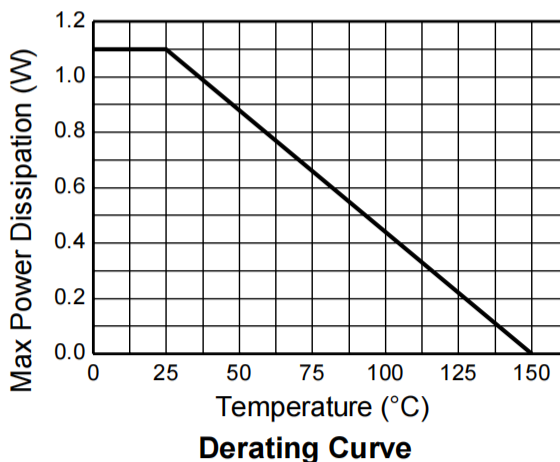
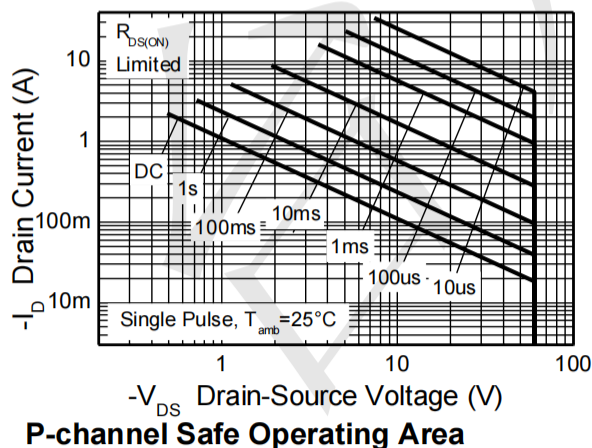
Characteristic		Symbol	Value	Unit
Power Dissipation Linear Derating Factor	(Note 5)	P _D	1.1	W mW/°C
			8.8	
	(Note 6)		1.92	
			15.4	
Thermal Resistance, Junction to Ambient	(Note 5)	R _{θJA}	113	°C/W
	(Note 6)		65	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

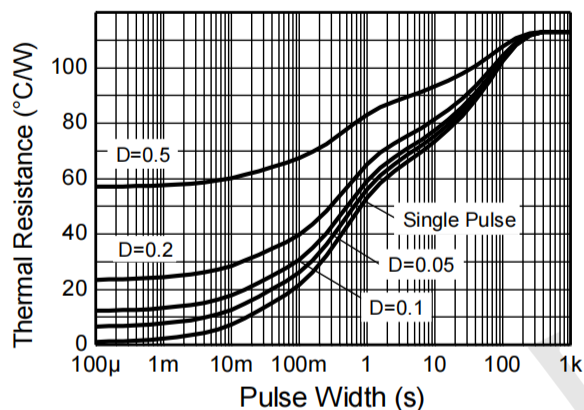
Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

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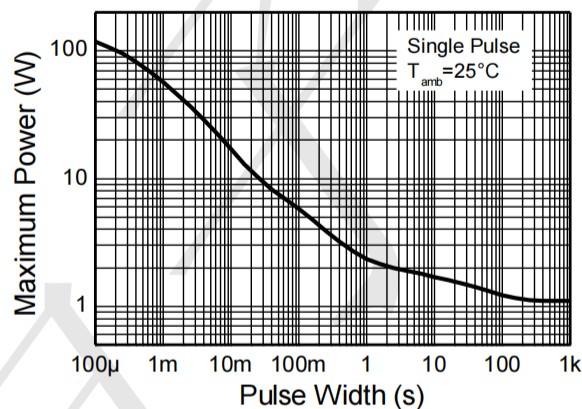
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV_{DSS}	-60	—	—	V	$I_D = -250\mu A$, $V_{GS} = 0V$	
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-1	μA	$V_{DS} = -48V$, $V_{GS} = 0V$	
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	$V_{GS(th)}$	-1	-1.5	-3	V	$I_D = -250\mu A$, $V_{DS} = V_{GS}$	
Static Drain-Source On-Resistance (Note 8)	$R_{DS(ON)}$	—	95	118	m Ω	$V_{GS} = -10V$, $I_D = -3A$	
			130	190		$V_{GS} = -4.5V$, $I_D = -1.9A$	
Forward Transconductance (Notes 8 & 9)	g_{fs}	—	4.7	—	S	$V_{DS} = -15V$, $I_D = -2.3A$	
Diode Forward Voltage (Note 8)	V_{SD}	—	-0.85	-0.95	V	$I_S = -2A$, $V_{GS} = 0V$	
Reverse Recovery Time (Note 9)	t_{rr}	—	25.1	—	ns	$I_F = -1.7A$, $di/dt = 100A/\mu s$	
Reverse Recovery Charge (Note 9)	Q_{rr}	—	27.2	—	nC		
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C_{iss}	—	637	—	pF	$V_{DS} = -30V$, $V_{GS} = 0V$ $f = 1MHz$	
Output Capacitance	C_{oss}	—	70	—	pF		
Reverse Transfer Capacitance	C_{rss}	—	53	—	pF		
Total Gate Charge (Note 10)	Q_g	—	9.8	—	nC	$V_{GS} = -5V$	$V_{DS} = -30V$ $I_D = -2.3A$
Total Gate Charge (Note 10)	Q_g	—	17.7	—	nC	$V_{GS} = -10V$	
Gate-Source Charge (Note 10)	Q_{gs}	—	1.6	—	nC		
Gate-Drain Charge (Note 10)	Q_{gd}	—	4.4	—	nC		
Turn-On Delay Time (Note 10)	$t_{D(on)}$	—	2.6	—	ns	$V_{DD} = -30V$, $V_{GS} = -10V$ $I_D = -1A$, $R_G \cong 6\Omega$	
Turn-On Rise Time (Note 10)	t_r	—	3.4	—	ns		
Turn-Off Delay Time (Note 10)	$t_{D(off)}$	—	26.2	—	ns		
Turn-Off Fall Time (Note 10)	t_f	—	11.3	—	ns		

Typical Performance Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise Specified)

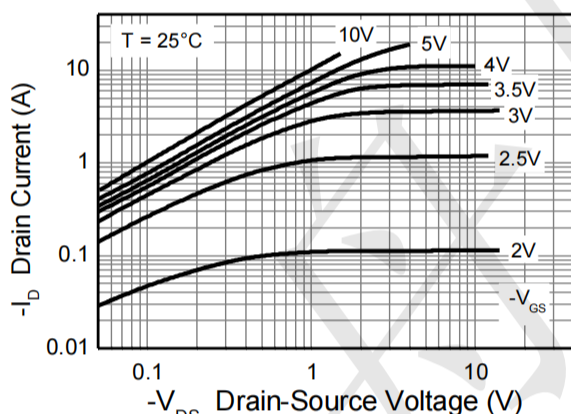




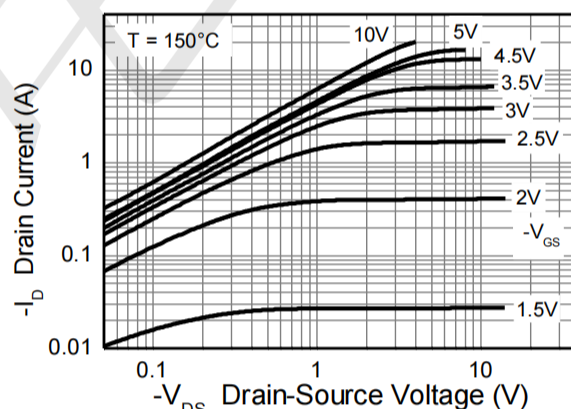
Transient Thermal Impedance



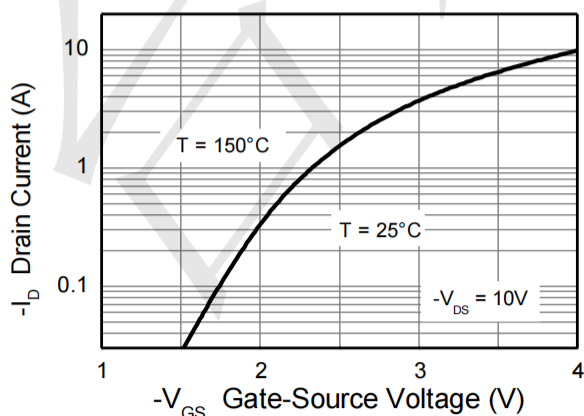
Pulse Power Dissipation



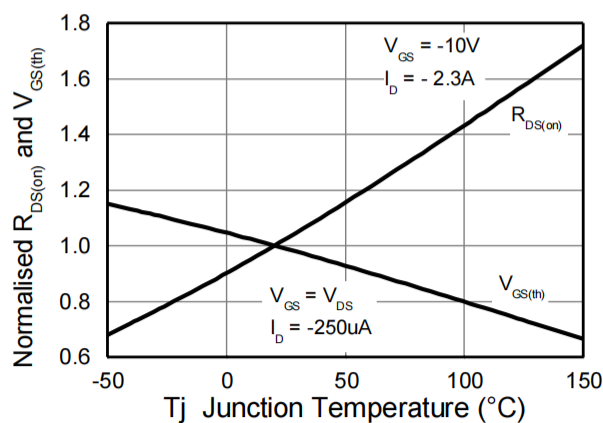
Output Characteristics



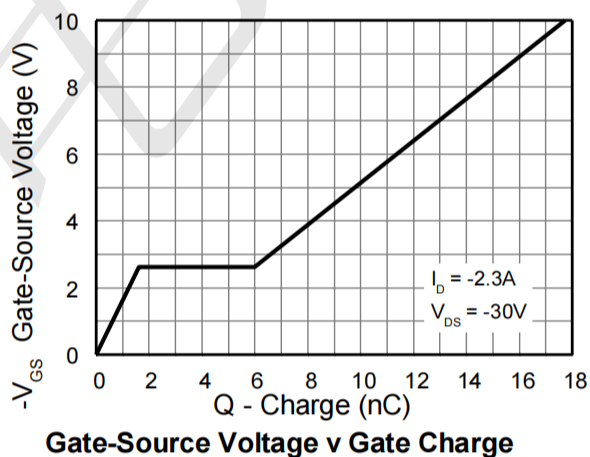
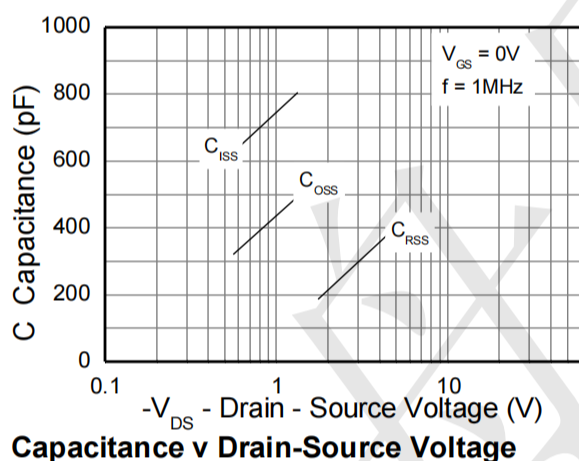
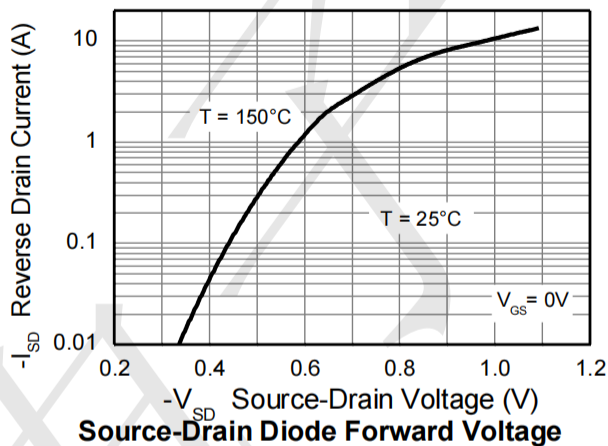
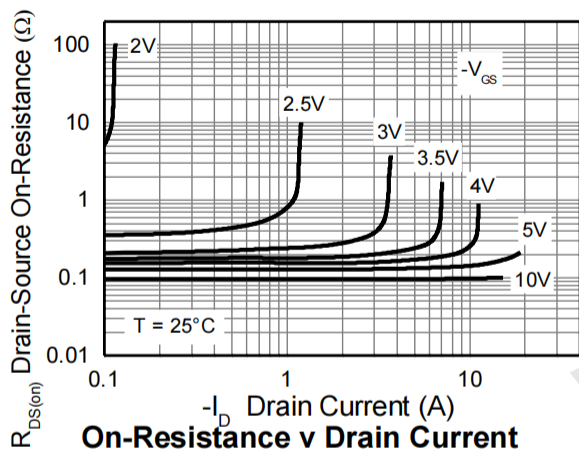
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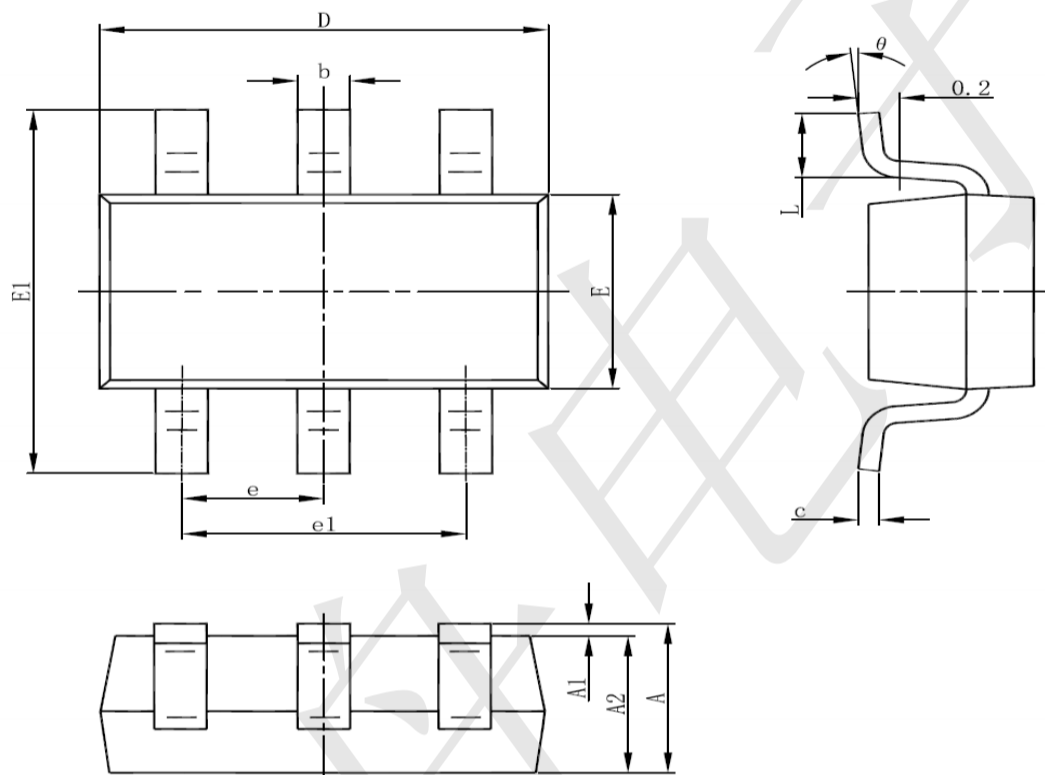
Typical Transfer Characteristics



Normalised Curves v Temperature



SOT23-6 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°